**TOSHIBA** 

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

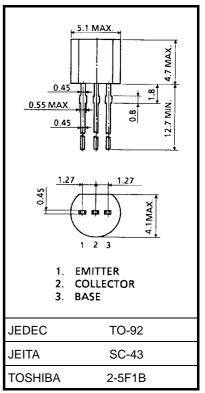
# 2SC2120

Audio Power Amplifier Applications

- High hFE: hFE (1) = 100~320
- 1 watts amplifier applications.
- Complementary to 2SA950

### Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	35	V
Collector-emitter voltage	V <sub>CEO</sub>	30	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	Ι <sub>C</sub>	800	mA
Base current	Ι <sub>Β</sub>	160	mA
Collector power dissipation	PC	600	mW
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C



Weight: 0.21 g (typ.)

## **Electrical Characteristics (Ta = 25°C)**

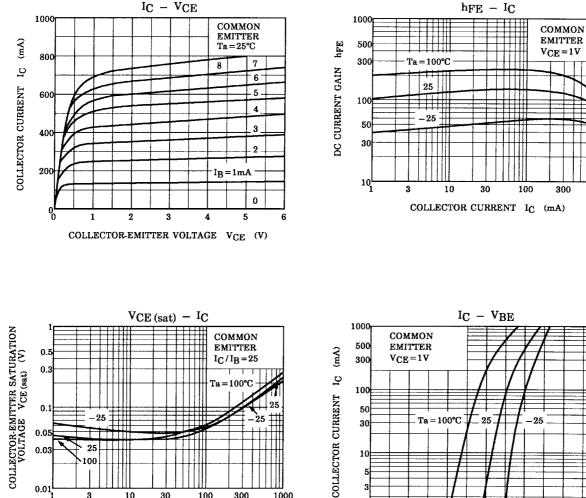
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 35 V, I_{E} = 0$	_		0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 5 V, I_{C} = 0$			0.1	μΑ
Collector-emitter breakdown voltage	V (BR) CEO	$I_{C} = 10 \text{ mA}, I_{B} = 0$	30	_	_	V
DC current gain	h <sub>FE (1)</sub> (Note)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 100 \text{ mA}$	100	_	320	
	h <sub>FE (2)</sub>	$V_{CE} = 1 \text{ V}, I_{C} = 700 \text{ mA}$	35	_	_	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	$I_{C} = 500 \text{ mA}, I_{B} = 20 \text{ mA}$	_	_	0.5	V
Base-emitter voltage	V <sub>BE</sub>	$V_{CE} = 1 \text{ V}, I_{C} = 10 \text{ mA}$	0.5	_	0.8	V
Transition frequency	fT	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$	_	120		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$		13	—	pF

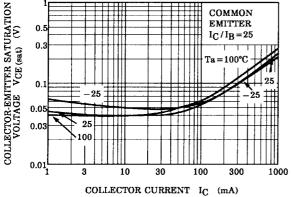
Note: hFE (1) classification O: 100~200, Y: 160~320

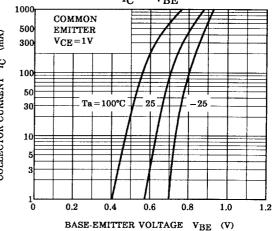
Unit: mm

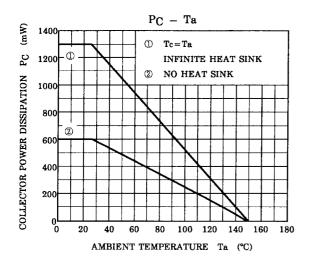
# TOSHIBA

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Handbook" etc.,

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